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Team Nexperia

74LVT241

3.3 V octal buffer/line driver; 3-state

Rev. 03 — 7 May 2008 Product data sheet

1. General description

The 74LVT241 high-performance BiCMOS device combines low static and dynamic power dissipation with high speed and high output drive.

This device is an octal buffer that is ideal for driving bus lines. The device features two output enables ($1\overline{OE}$, 2OE), each controlling four of the 3-state outputs.

2. Features

- 3-state buffers
- Octal bus interface
- Input and output interface capability to systems at 5 V supply
- TTL input and output switching levels
- Output capability: +64 mA/–32 mA
- Latch-up protection exceeds 500 mA per JESD78 class II level A
- ESD protection:
  - HBM JESD22-A114E exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V
- Bus-hold data inputs eliminate the need for external pull-up resistors for unused inputs
- Live insertion/extraction permitted
- Power-up 3-state
- No bus current loading when output is tied to 5 V bus

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74LVT241D	–40 °C to +85 °C	SO20	plastic small outline package; 20 leads; body width 7.5 mm	SOT163-1
74LVT241DB	–40 °C to +85 °C	SSOP20	plastic shrink small outline package; 20 leads; body width 5.3 mm	SOT339-1
74LVT241PW	–40 °C to +85 °C	TSSOP20	plastic thin shrink small outline package; 20 leads; body width 4.4 mm	SOT360-1
74LVT241BQ	–40 °C to +85 °C	DHVQFN20	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 20 terminals; body 2.5 × 4.5 × 0.85 mm	SOT764-1

4. Functional diagram

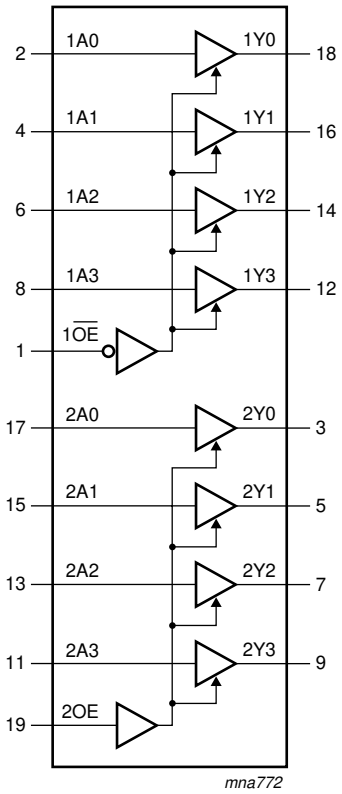


Fig 1. Logic symbol

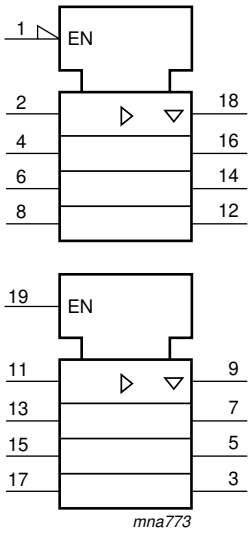


Fig 2. IEC logic symbol

5. Pinning information

5.1 Pinning

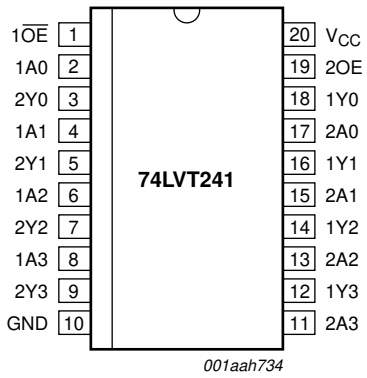
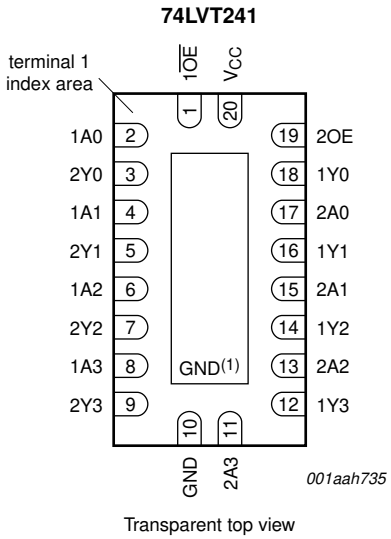


Fig 3. Pin configuration for SO20 and (T)SSOP20



Transparent top view

(1) The die substrate is attached to this pad using conductive die attach material. It can not be used as a supply pin or input.

Fig 4. Pin configuration for DHVQFN20

5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
$1\overline{OE}$	1	output enable input (active LOW)
1A0 to 1A3	2, 4, 6, 8	data input
2A0 to 2A3	17, 15, 13, 11	data input
GND	10	ground (0 V)
1Y0 to 1Y3	18, 16, 14, 12	data output
2Y0 to 2Y3	3, 5, 7, 9	data output
2OE	19	output enable input (active HIGH)
V_{CC}	20	supply voltage

6. Functional description

Table 3. Function table

Inputs				Outputs	
$1\overline{OE}$	2OE	1An	2An	1Yn	2Yn
L	H	L	L	L	L
L	H	H	H	H	H
H	L	X	X	Z	Z

[1] H = HIGH voltage level;
L = LOW voltage level;
X = Don't care;
Z = High impedance "OFF" state.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).[1]

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			−0.5	+4.6	V
V_I	input voltage		[2]	−0.5	+7.0	V
V_O	output voltage	output in OFF or HIGH state	[2]	−0.5	+7.0	V
I_{IK}	input clamping current	$V_I < 0$ V		−50	-	mA
I_{OK}	output clamping current	$V_O < 0$ V		−50	-	mA
I_O	output current	output in LOW state		-	128	mA
		output in HIGH state		−64	-	mA
T_{stg}	storage temperature			−65	+150	°C
T_j	junction temperature			-	+150	°C
P_{tot}	total power dissipation	T_{amb} = −40 °C to +85 °C	[3]	-	500	mW

[1] The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability. The maximum junction temperature of this integrated circuit should not exceed 150 °C.

[2] The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.

[3] For SO20 packages: above 70 °C derate linearly with 8 mW/K.
For SSOP20 and TSSOP20 packages: above 60 °C derate linearly with 5.5 mW/K.
For DHVQFN20 packages: above 60 °C derate linearly with 4.5 mW/K.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		2.7	3.6	V
V_I	input voltage		0	5.5	V
I_{OH}	HIGH-level output current		−32	-	mA

Table 5. Recommended operating conditions *…continued*

Symbol	Parameter	Conditions	Min	Max	Unit
I_{OL}	LOW-level output current		-	32	mA
		current duty cycle ≤ 50 %; $f_i \geq 1$ kHz	-	64	mA
T_{amb}	ambient temperature	in free air	−40	+85	°C
$\Delta t/\Delta V$	input transition rise and fall rate	output enabled	0	10	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V); T_{amb} = −40 °C to +85 °C.

Symbol	Parameter	Conditions		Min	Typ[1]	Max	Unit
V_{IK}	input clamping voltage	V_{CC} = 2.7 V; I_{IK} = −18 mA		−1.2	−0.9	-	V
V_{IH}	HIGH-level input voltage			2.0	-	-	V
V_{IL}	LOW-level input voltage			-	-	0.8	V
V_{OH}	HIGH-level output voltage	V_{CC} = 2.7 V to 3.6 V; I_{OH} = −100 µA		V_{CC} − 0.2	V_{CC} − 0.1	-	V
		V_{CC} = 2.7 V; I_{OH} = −8 mA		2.4	2.5	-	V
		V_{CC} = 3.0 V; I_{OH} = −32 mA		2.0	2.2	-	V
V_{OL}	LOW-level output voltage	V_{CC} = 2.7 V; I_{OL} = 100 µA			0.1	0.2	V
		V_{CC} = 2.7 V; I_{OL} = 24 mA		-	0.3	0.5	V
		V_{CC} = 3.0 V; I_{OL} = 16 mA		-	0.25	0.4	V
		V_{CC} = 3.0 V; I_{OL} = 32 mA		-	0.3	0.5	V
		V_{CC} = 3.0 V; I_{OL} = 64 mA		-	0.4	0.55	V
I_I	input leakage current	control and data pins					
		V_{CC} = 0 V or 3.6 V; V_I = 5.5 V		-	1	10	µA
		control pins					
		V_{CC} = 3.6 V; V_I = V_{CC} or GND		-	0.1	±1	µA
		data pins	[2]				
		V_{CC} = 3.6 V; V_I = V_{CC}		-	0.1	1	µA
		V_{CC} = 3.6 V; V_I = 0 V		−5	−1	-	µA
I_{OFF}	power-off leakage current	V_{CC} = 0 V; V_I or V_O = 0 V to 4.5 V		-	1	±100	µA
I_{BHL}	bus hold LOW current	V_{CC} = 3.0 V; V_I = 0.8 V		75	150	-	µA
I_{BHH}	bus hold HIGH current	V_{CC} = 3.0 V; V_I = 2.0 V		-	−150	−75	µA
I_{BHLO}	bus hold LOW overdrive current	V_{CC} = 3.6 V; V_I = 0 V to 3.6 V	[3]	500	-	-	µA
I_{BHHO}	bus hold HIGH overdrive current	V_{CC} = 3.6 V; V_I = 0 V to 3.6 V	[3]	-	-	−500	µA
I_{LO}	output leakage current	V_O = 5.5 V; V_{CC} = 3.0 V; output HIGH		-	60	125	µA
$I_{O(pu/pd)}$	power-up/power-down output current	$V_{CC} \leq$ 1.2 V; V_O = 0.5 V to V_{CC}; V_I = GND or V_{CC}; $1\overline{OE}$, 2OE = don't care	[4]	-	±1	±100	µA
I_{OZ}	OFF-state output current	V_{CC} = 3.6 V; V_O = 3.0 V		-	1	5	µA
		V_{CC} = 3.6 V; V_O = 0.5 V		−5	−1	-	µA

Table 6. Static characteristics *...continued*

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V); T_{amb} = −40 °C to +85 °C.

Symbol	Parameter	Conditions		Min	Typ[1]	Max	Unit
I_{CC}	supply current	V_{CC} = 3.6 V; V_I = V_{CC} or GND; I_O = 0 A					
		outputs HIGH		-	0.12	0.19	mA
		outputs LOW		-	3	12	mA
		outputs disabled	[5]	-	0.12	0.19	mA
ΔI_{CC}	additional supply current	per input pin; V_{CC} = 3.0 V to 3.6 V; one input = V_{CC} − 0.6 V other inputs at V_{CC} or GND	[6]	-	0.1	0.25	mA
C_I	input capacitance	$1\overline{OE}$ and 2OE inputs; outputs disabled; V_I = 0 V or 3.0 V		-	4	-	pF
$C_{I/O}$	input/output capacitance	at input/output data pins, outputs disabled; $V_{I/O}$ = 0 V or 3.0 V		-	8	-	pF

[1] All typical values are measured at T_{amb} = 25 °C.

[2] Unused pins at V_{CC} or GND.

[3] This is the bus hold overdrive current required to force the input to the opposite logic state.

[4] This parameter is valid for any V_{CC} between 0 V and 1.2 V with a transition time of up to 10 ms. From V_{CC} = 1.2 V to V_{CC} = 3.3 V ± 0.3 V a transition time of 100 ms is permitted. This parameter is valid for T_{amb} = +25 °C only.

[5] I_{CC} with the outputs disabled is measured with outputs pulled to V_{CC} or GND.

[6] This is the increase in supply current for each input at the specified voltage level other than V_{CC} or GND.

10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V). For test circuit see Figure 8; T_{amb} = −40 °C to +85 °C.

Symbol	Parameter	Conditions	Min	Typ[1]	Max	Unit
t_{PLH}	LOW to HIGH propagation delay	1An to 1Yn, 2An to 2Yn; see Figure 5				
		V_{CC} = 2.7 V	-	-	4.0	ns
		V_{CC} = 3.3 V ± 0.3 V	1.0	2.8	3.8	ns
t_{PHL}	HIGH to LOW propagation delay	1An to 1Yn, 2An to 2Yn; see Figure 5				
		V_{CC} = 2.7 V	-	-	4.0	ns
		V_{CC} = 3.3 V ± 0.3 V	1.0	2.8	3.8	ns
t_{PZH}	OFF-state to HIGH propagation delay	$1\overline{OE}$ to 1Yn; see Figure 6				
		V_{CC} = 2.7 V	-	-	5.0	ns
		V_{CC} = 3.3 V ± 0.3 V	1.0	3.2	4.4	ns
		2OE to 2Yn; see Figure 7				
		V_{CC} = 2.7 V	-	-	5.6	ns
		V_{CC} = 3.3 V ± 0.3 V	1.0	3.8	5.1	ns

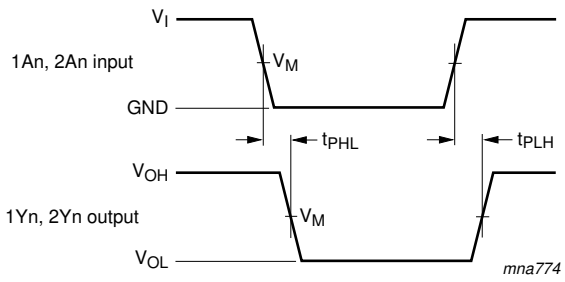
Table 7. Dynamic characteristics *...continued*

Voltages are referenced to GND (ground = 0 V). For test circuit see Figure 8; T_{amb} = −40 °C to +85 °C.

Symbol	Parameter	Conditions	Min	Typ[1]	Max	Unit
t_{PZL}	OFF-state to LOW propagation delay	$1\overline{OE}$ to 1Yn; see Figure 6				
		V_{CC} = 2.7 V	-	-	4.9	ns
		V_{CC} = 3.3 V ± 0.3 V	1.0	3.1	4.3	ns
		2OE to 2Yn; see Figure 7				
		V_{CC} = 2.7 V	-	-	5.4	ns
		V_{CC} = 3.3 V ± 0.3 V	1.0	3.8	5.0	ns
t_{PHZ}	HIGH to OFF-state propagation delay	$1\overline{OE}$ to 1Yn; see Figure 6				
		V_{CC} = 2.7 V	-	-	5.4	ns
		V_{CC} = 3.3 V ± 0.3 V	2.0	3.6	5.2	ns
		2OE to 2Yn; see Figure 7				
		V_{CC} = 2.7 V	-	-	5.0	ns
		V_{CC} = 3.3 V ± 0.3 V	1.0	3.1	4.5	ns
t_{PLZ}	LOW to OFF-state propagation delay	$1\overline{OE}$ to 1Yn; see Figure 6				
		V_{CC} = 2.7 V	-	-	4.3	ns
		V_{CC} = 3.3 V ± 0.3 V	1.6	2.9	4.2	ns
		2OE to 2Yn; see Figure 7				
		V_{CC} = 2.7 V	-	-	4.3	ns
		V_{CC} = 3.3 V ± 0.3 V	1.0	2.8	4.0	ns

[1] Typical values are measured at T_{amb} = 25 °C and V_{CC} = 3.3 V.

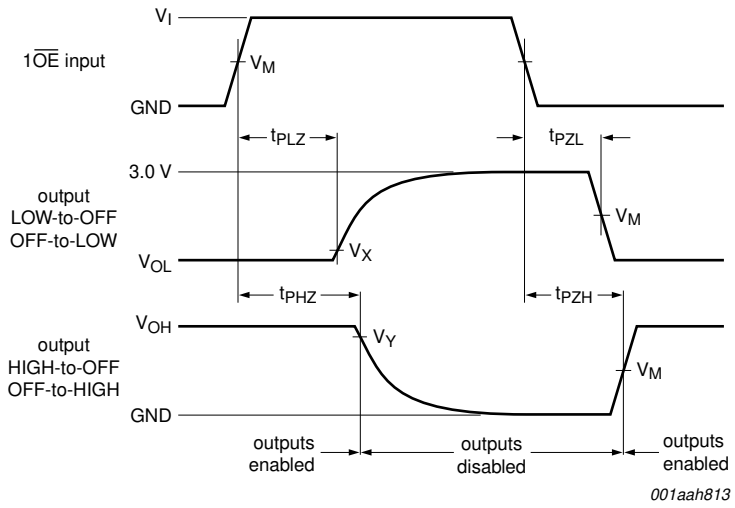
11. Waveforms



See Table 8 for measurement points.

V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

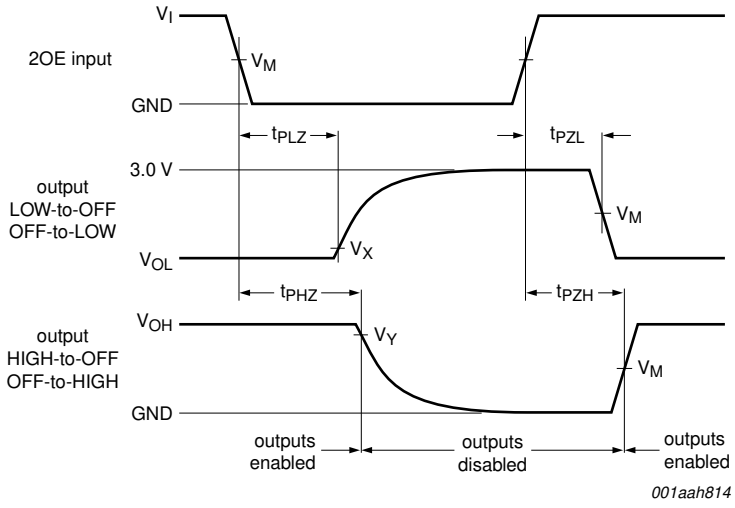
Fig 5. Input (1An, 2An) to output (1Yn, 2Yn) propagation delays and output transition times



See Table 8 for measurement points.

V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 6. 3-state output enable and disable times



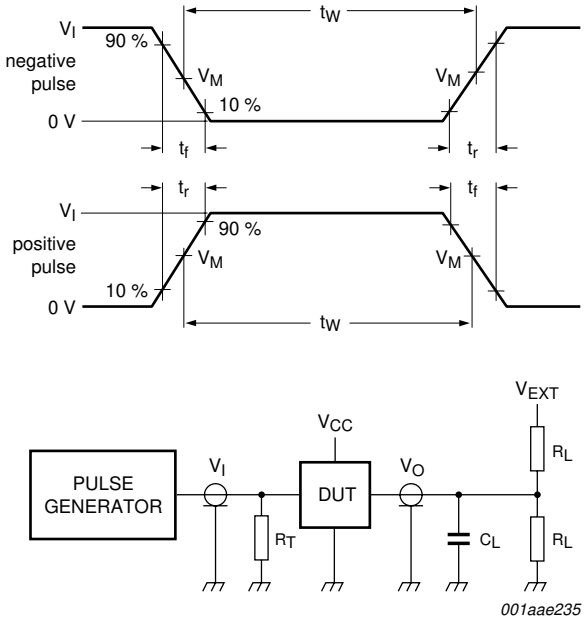
See Table 8 for measurement points.

V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 7. 3-state output enable and disable times

Table 8. Measurement points

V_{CC}	Input	Output		
	V_M	V_X	V_Y	V_M
2.7 V to 3.6 V	1.5 V	V_{OL} + 0.3 V	V_{OH} − 0.3 V	1.5 V



Test data is given in Table 9.

Definitions test circuit:

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

V_{EXT} = External voltage for measuring switching times.

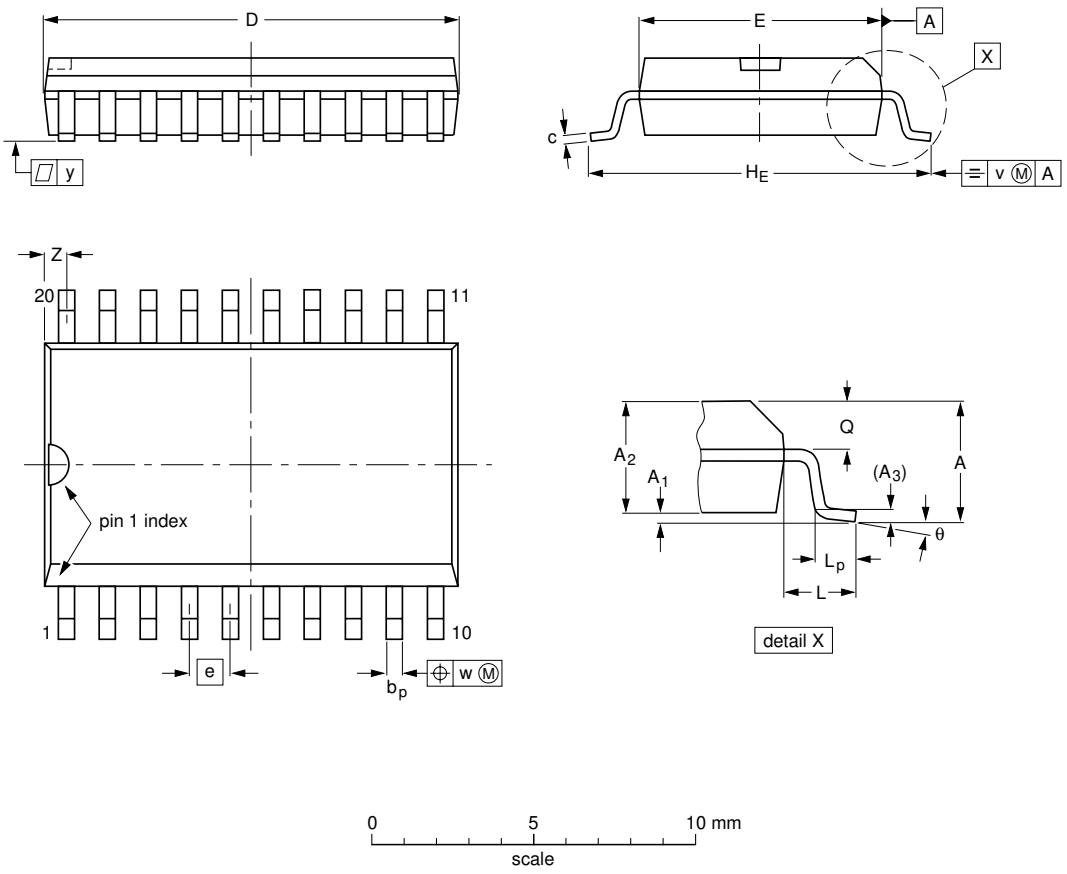
Fig 8. Test circuit for switching times

Table 9. Test data

Input				Load		V_{EXT}		
V_I	f_i	t_W	t_r, t_f	R_L	C_L	t_{PHZ}, t_{PZH}	t_{PLZ}, t_{PZL}	t_{PLH}, t_{PHL}
2.7 V	≤ 10 MHz	500 ns	≤ 2.5 ns	500 Ω	50 pF	GND	6 V	open

12. Package outline

SO20: plastic small outline package; 20 leads; body width 7.5 mm **SOT163-1**



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (1)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	2.65	0.3 0.1	2.45 2.25	0.25	0.49 0.36	0.32 0.23	13.0 12.6	7.6 7.4	1.27	10.65 10.00	1.4	1.1 0.4	1.1 1.0	0.25	0.25	0.1	0.9 0.4	8° 0°
inches	0.1	0.012 0.004	0.096 0.089	0.01	0.019 0.014	0.013 0.009	0.51 0.49	0.30 0.29	0.05	0.419 0.394	0.055	0.043 0.016	0.043 0.039	0.01	0.01	0.004	0.035 0.016	

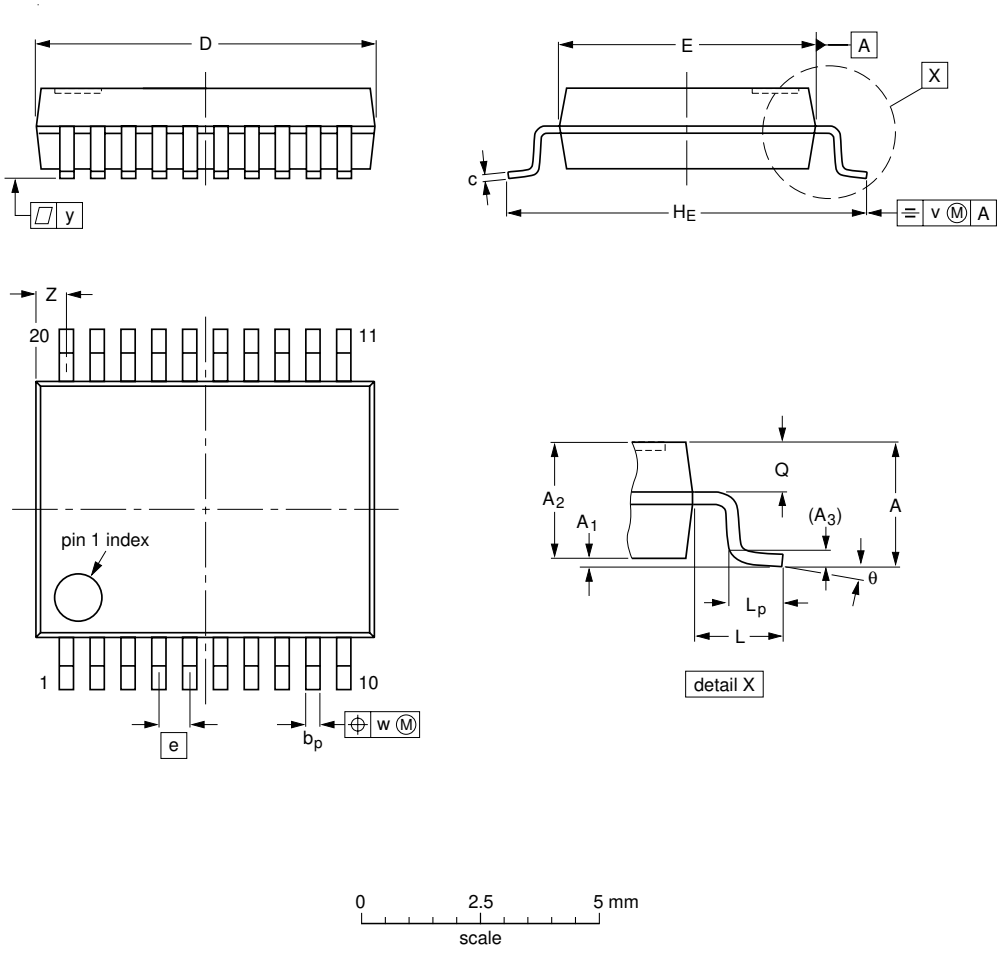
Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT163-1	075E04	MS-013				~~99-12-27~~ 03-02-19

Fig 9. Package outline SOT163-1 (SO20)

SSOP20: plastic shrink small outline package; 20 leads; body width 5.3 mm **SOT339-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	2	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	7.4 7.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	0.9 0.5	8^o 0^o

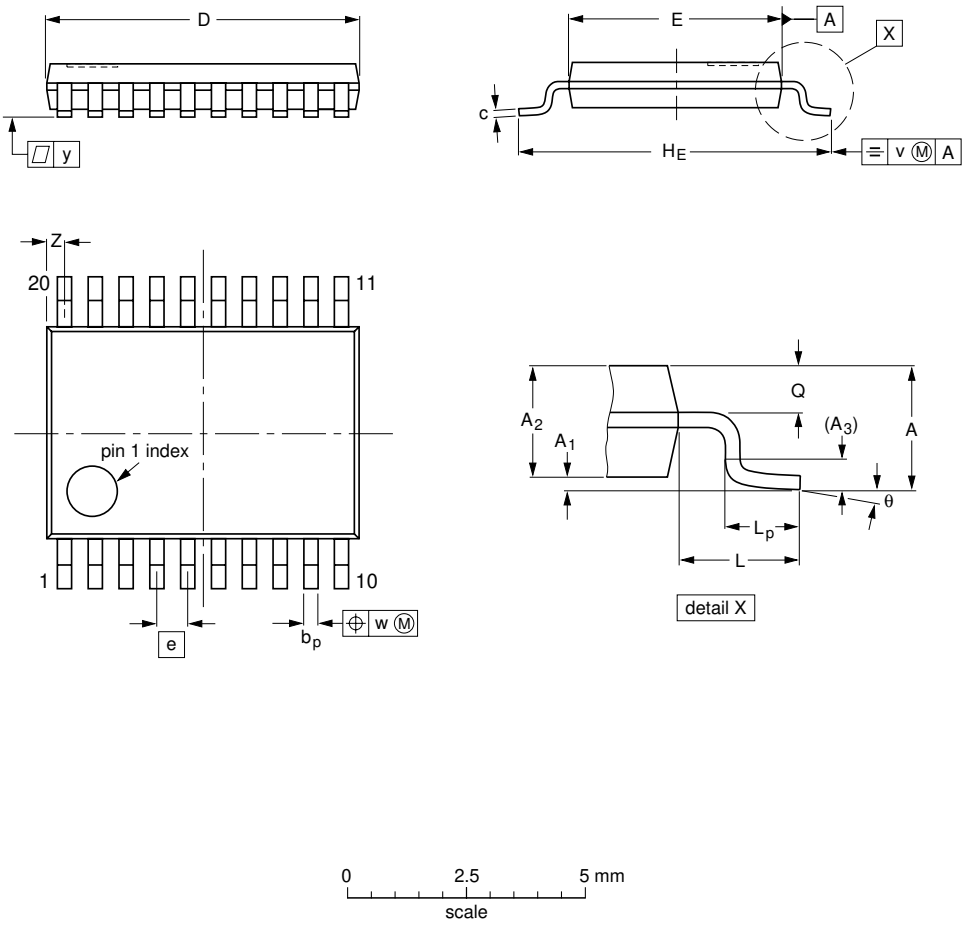
Note

1. Plastic or metal protrusions of 0.2 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT339-1		MO-150				~~99-12-27~~ 03-02-19

Fig 10. Package outline SOT339-1 (SSOP20)

TSSOP20: plastic thin shrink small outline package; 20 leads; body width 4.4 mm **SOT360-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (2)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	6.6 6.4	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.5 0.2	8° 0°

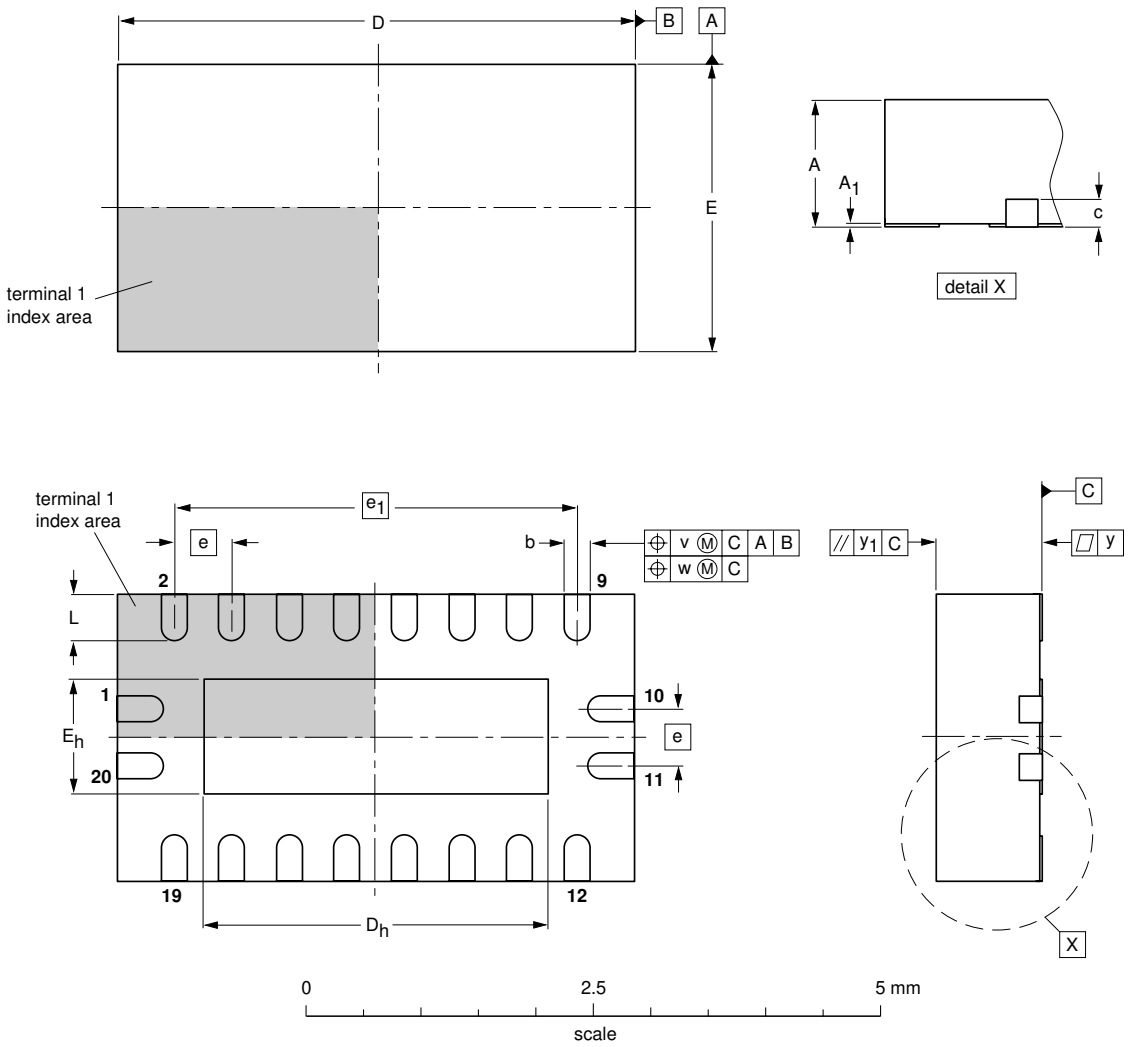
Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT360-1		MO-153				~~99-12-27~~ 03-02-19

Fig 11. Package outline SOT360-1 (TSSOP20)

DHVQFN20: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 20 terminals; body 2.5 x 4.5 x 0.85 mm **SOT764-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A(1) max.	A_1	b	c	D(1)	D_h	E(1)	E_h	e	e_1	L	v	w	y	y_1
mm	1	0.05 0.00	0.30 0.18	0.2	4.6 4.4	3.15 2.85	2.6 2.4	1.15 0.85	0.5	3.5	0.5 0.3	0.1	0.05	0.05	0.1

Note

1. Plastic or metal protrusions of 0.075 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT764-1	- - -	MO-241	- - -			~~02-10-17~~ 03-01-27

Fig 12. Package outline SOT764-1 (DHVQFN20)

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
BiCMOS	Bipolar Complementary Metal Oxide Semiconductor
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVT241_3	20080507	Product data sheet	ECN07_046	74LVT241_2
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • DHVQFN20 package added Section 3 “Ordering information” and Section 12 “Package outline”.			
74LVT241_2	19980219	Product specification	-	74LVT241_1
74LVT241_1	19960529	Product specification	-	-

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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17. Contents

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